

AM4481P-T1-PF-VB Datasheet

P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 100	0.160 at $V_{GS} = - 10$ V	- 2.5 ^c	23.2 nC
	0.200 at $V_{GS} = - 4.5$ V	- 2.3 ^c	

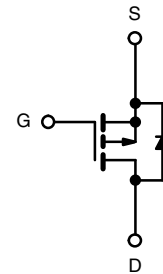
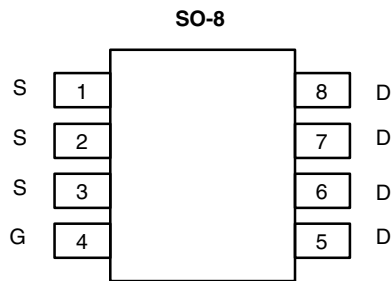
FEATURES

- Trench Power MOSFET
- 100% R_g and UIS Tested


RoHS
 COMPLIANT

APPLICATIONS

- Active Clamp in Intermediate DC/DC Power Supplies
- H-Bridge High Side Switch for Lighting Application



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	- 2.5	A
	$T_C = 70$ °C	- 2.3	
	$T_A = 25$ °C	- 2 ^{a, b}	
	$T_A = 70$ °C	- 1.6 ^{a, b}	
Pulsed Drain Current	I_{DM}	- 15	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	- 4.9	
	$T_A = 25$ °C	- 2.5 ^{a, b}	
Avalanche Current	I_{AS}	- 15	mJ
Single-Pulse Avalanche Energy	E_{AS}	11.25	
Maximum Power Dissipation	$T_C = 25$ °C	5.9	W
	$T_C = 70$ °C	3.8	
	$T_A = 25$ °C	3.1 ^{a, b}	
	$T_A = 70$ °C	2 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

Notes:

a. Surface mounted on 1" x 1" FR4 board.

 b. $t = 10$ s.

 c. Based on $T_C = 25$ °C.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	R_{thJA}	33	40	°C/W
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	21	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Maximum under steady state conditions is 80 °C/W.

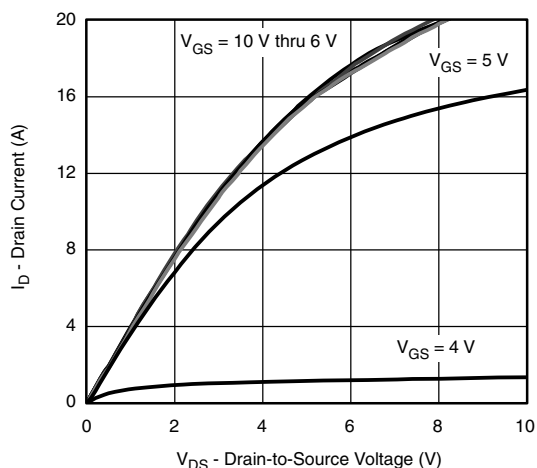
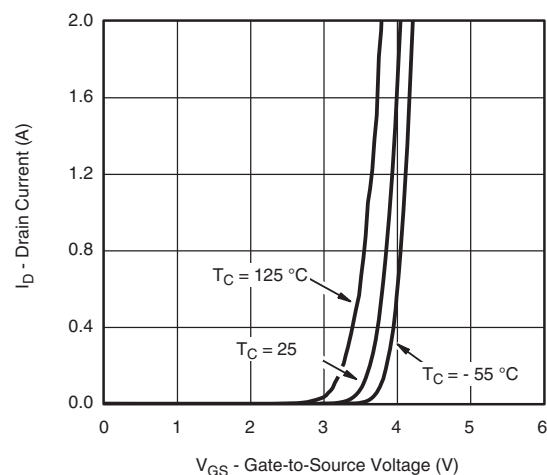
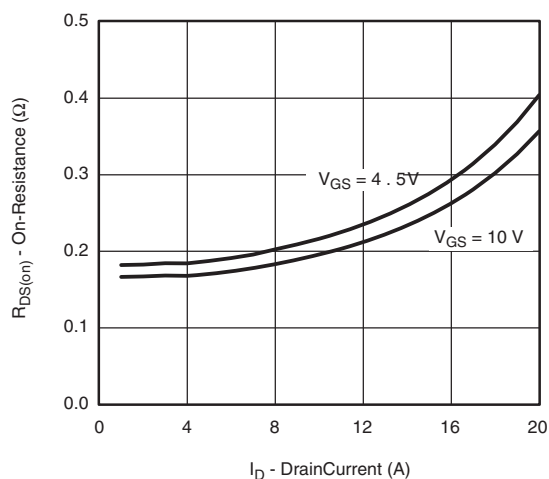
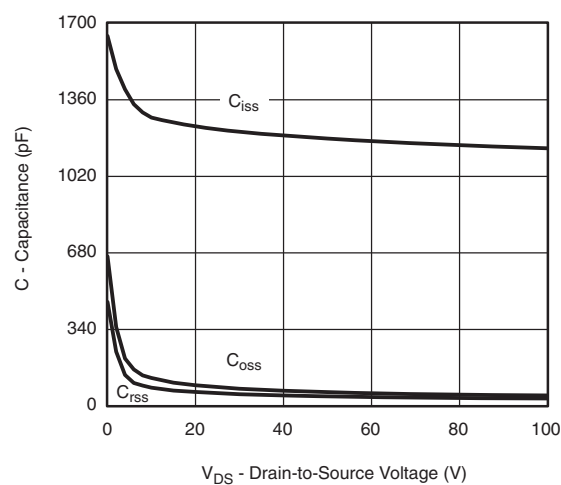
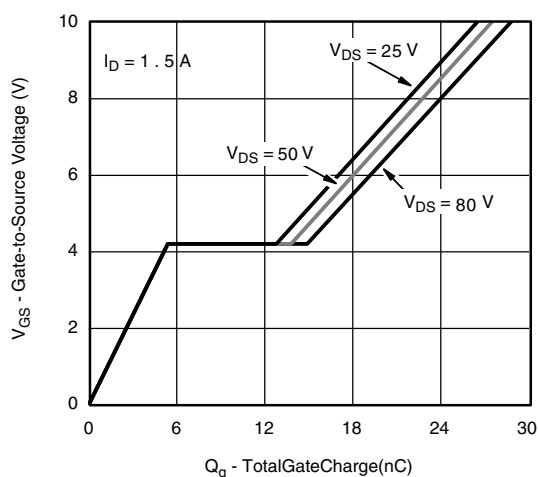
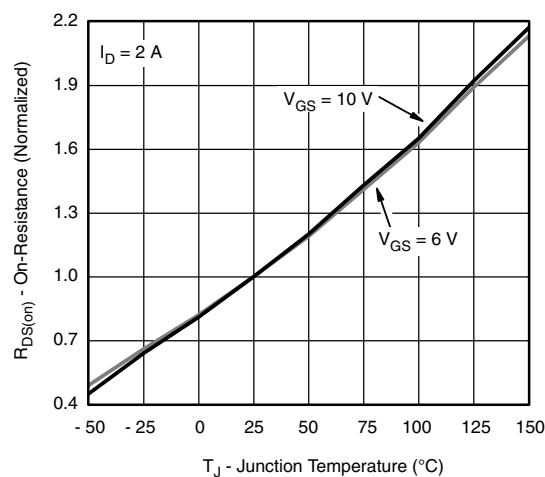
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 100			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 165		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6.6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 100 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 5 V, V _{GS} = - 10 V	- 8			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 2 A		0.160		Ω
		V _{GS} = - 4.5V, I _D = - 1.5 A		0.200		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = 2 A		12		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 50 V, V _{GS} = 0 V, f = 1 MHz		1190		pF
Output Capacitance	C _{oss}			61		
Reverse Transfer Capacitance	C _{rss}			42		
Total Gate Charge	Q _g	V _{DS} = - 50 V, V _{GS} = - 10 V, I _D = - 2 A		27.5	42	nC
		V _{DS} = - 50 V, V _{GS} = - 6 V, I _D = - 2 A		23.2	35	
Gate-Source Charge	Q _{gs}			5.4		
Gate-Drain Charge	Q _{gd}			8.4		
Gate Resistance	R _g	f = 1 MHz		6.1	9.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 75 V, R _L = 25 Ω I _D ≅ - 3 A, V _{GEN} = - 6 V, R _g = 1 Ω		20	30	ns
Rise Time	t _r			95	145	
Turn-Off DelayTime	t _{d(off)}			38	60	
Fall Time	t _f			34	51	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 75 V, R _L = 25 Ω I _D ≅ - 2 A, V _{GEN} = - 10 V, R _g = 1 Ω		11	18	
Rise Time	t _r			28	42	
Turn-Off DelayTime	t _{d(off)}			52	78	
Fall Time	t _f			35	53	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 13	A
Pulse Diode Forward Current ^a	I _{SM}				- 15	
Body Diode Voltage	V _{SD}	I _S = - 2 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 4 A, dI/dt = 100 A/μs, T _J = 25 °C		65	90	ns
Body Diode Reverse Recovery Charge	Q _{rr}			180	270	nC
Reverse Recovery Fall Time	t _a			45		ns
Reverse Recovery Rise Time	t _b			20		

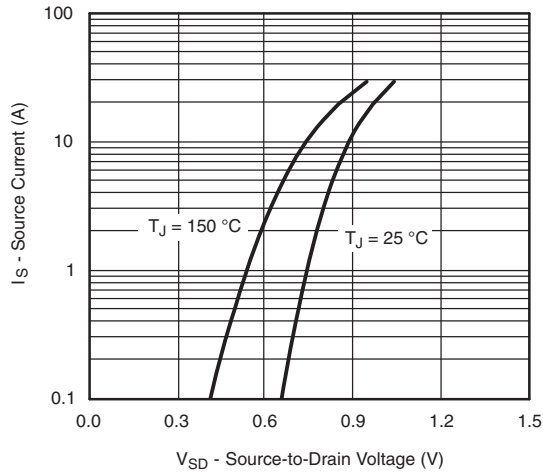
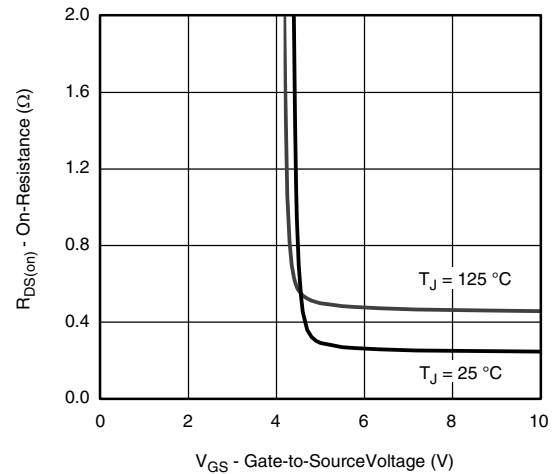
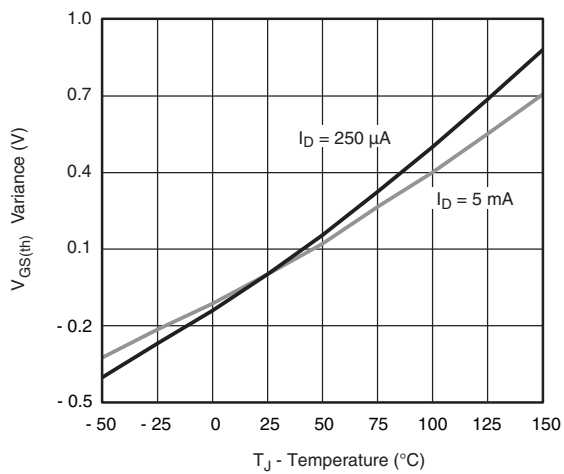
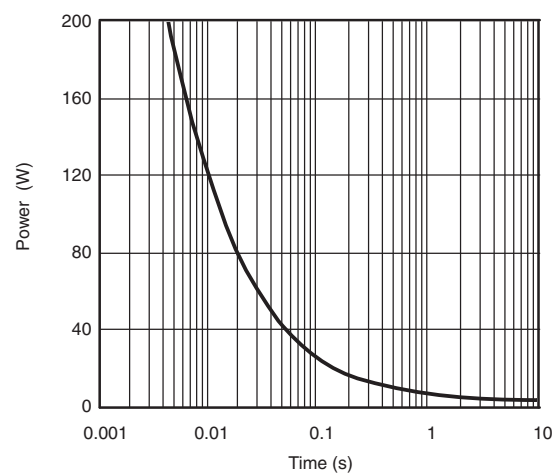
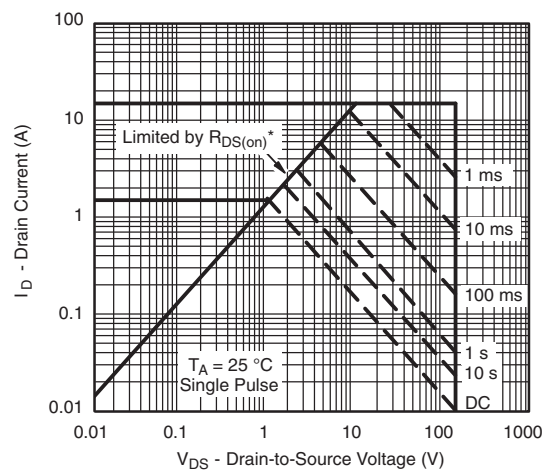
Notes:

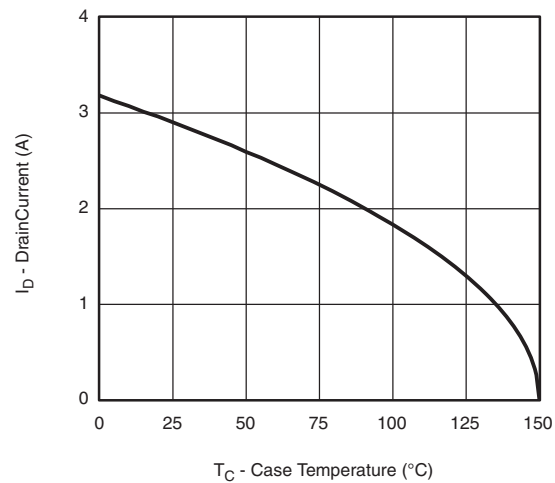
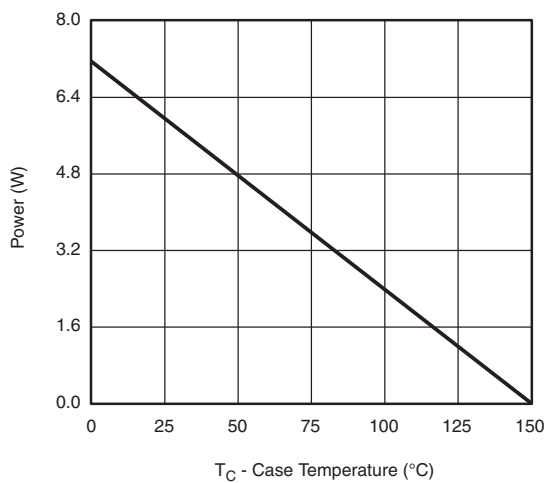
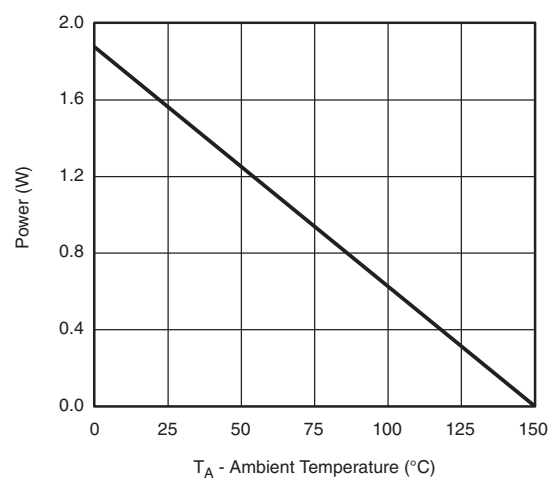
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

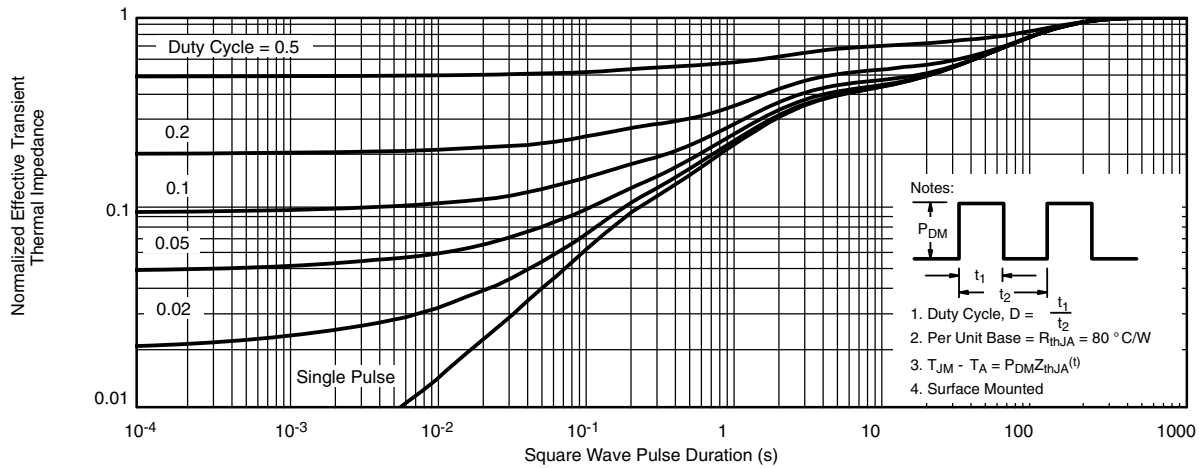
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

Safe Operating Area, Junction-to-Ambient

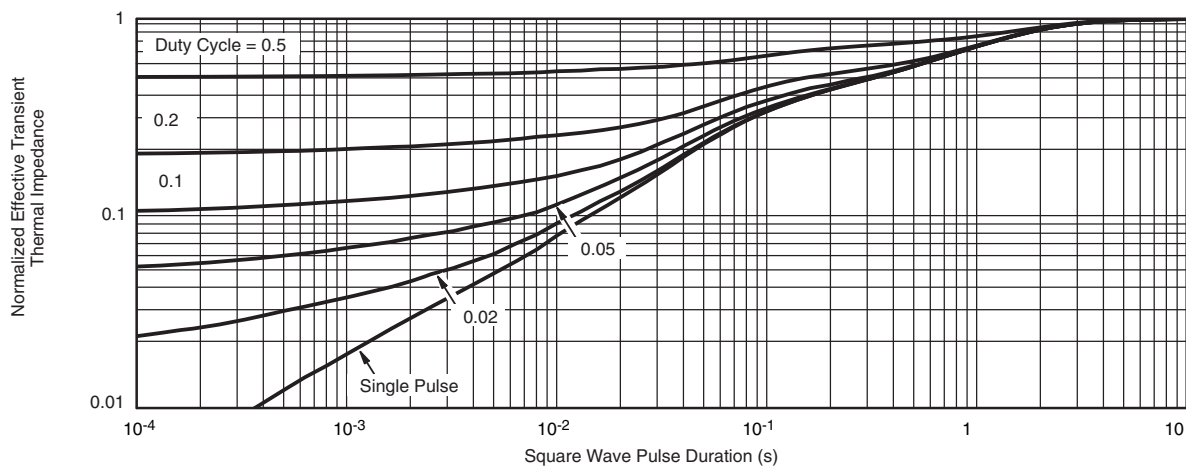
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Foot

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



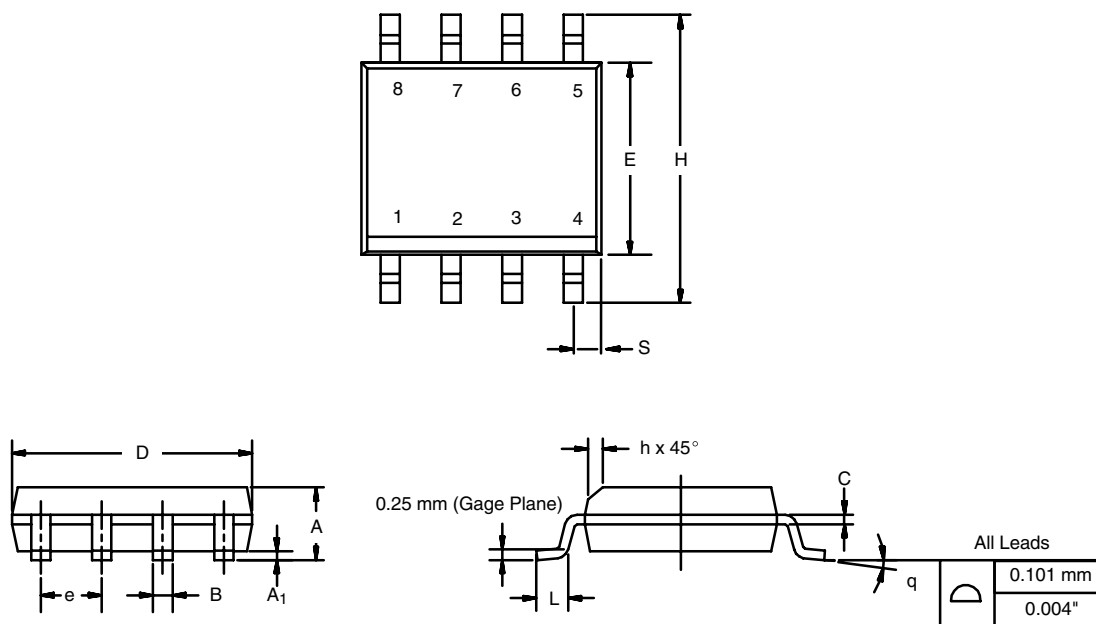
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

服务热线：400-655-8788

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